



January, 2006

FPAB30PH60

Smart Power Module for Front-End Rectifier

General Description

FPAB30PH60 is an advanced smart power module of PFC(Power Factor Correction) that Fairchild has newly developed and designed mainly targeting mid-power application especially for an air conditioners. It combines optimized circuit protection and drive IC matched to high frequency switching IGBTs. System reliability is futher enhanced by the integrated under-voltage lock-out and over-current protection function.

Features

- Low thermal resistance due to Al₂O₃-DBC substrate
- 600V-30A 2-phase IGBT PWM semi-converter including a drive IC for gate driving and protection
- · Typical switching frequency of 20kHz
- Isolation rating of 2500Vrms/min.

Applications

• AC 180V ~ 264V single-phase front-end rectifier

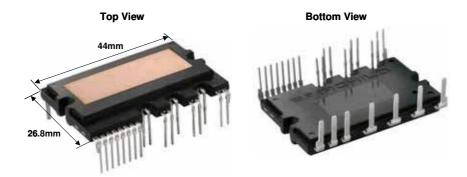


Fig. 1.

Integrated Power Functions

• PFC converter for single-phase AC/DC power conversion (Please refer to Fig. 3)

Integrated Drive, Protection and System Control Functions

- · For IGBTs: Gate drive circuit, Overcurrent circuit protection (OC), Control supply circuit under-voltage (UV) protection
- Fault signaling: Corresponding to a UV fault
- Input interface: 5V CMOS/LSTTL compatible, Schmitt trigger input

Pin Configuration

Top View

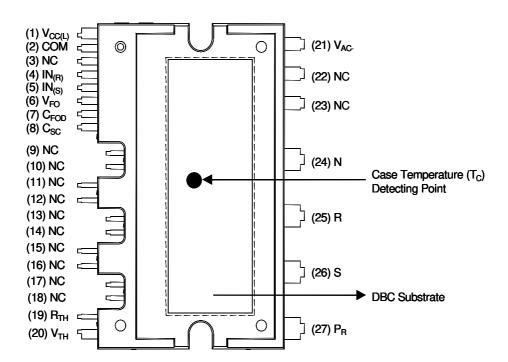
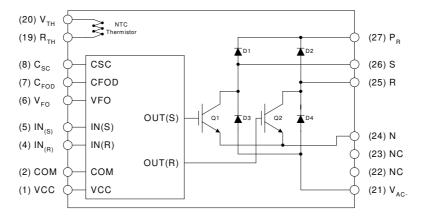


Fig. 2.

Pin Descriptions

Pin Number	Pin Name	Pin Description	
1	V _{CC}	Common Bias Voltage for IC and IGBTs Driving	
2	COM	Common Supply Ground	
4	IN _(R)	Signal Input for Low-side R-phase IGBT	
5	IN _(S)	Signal Input for Low-side S-phase IGBT	
6	V _{FO}	Fault Output	
7	C _{FOD}	Capacitor for Fault Output Duration Time Selection	
8	C _{SC}	Capacitor (Low-pass Filter) for Over Current Detection	
19	R _(TH)	NTC Thermistor terminal	
20	V _(TH)	NTC Thermistor terminal	
21	V _{AC-}	Negative Terminal of DC-Link (DIODE) for Sensing	
24	N	Negative Rail of DC-Link (IGBT)	
25	R	utput for R Phase	
26	S	Dutput for S Phase	
27	P _R	Positive Rail of DC-Link	
3, 9~18, 22~23	NC	No Connection	

Internal Equivalent Circuit and Input/Output Pins



Note:
1) Converter is composed of two IGBTs including four diodes and one IC which has gate driving and protection functions.

Fig. 3.

Absolute Maximum Ratings ($T_J = 25$ °C, Unless Otherwise Specified)

Converter Part

Item	Symbol	Condition	Rating	Unit
Supply Voltage	V _i	Applied between R-S	264	V_{RMS}
Supply Voltage (Surge)	V _{i(Surge)}	Applied between R-S	500	V
Output Voltage	V _{PN}	Applied between P- N	450	V
Output Voltage (Surge)	V _{PN(Surge)}	Applied between P- N	500	V
Collector-emitter Voltage	V _{CES}		600	V
Input Current (100% Load)	l _i	T _C < 95°C, V _i =220V, V _{PN} = 390V, V _{PWM} =20kHz	20	А
Input Current (125% Load)	I _{i(125%)}	T _C < 95°C, V _i =220V, V _{PN} = 390V, V _{PWM} =20kHz, 1min Non-repetitive	25	А
Collector Dissipation	P _C	T _C = 25°C per One IGBT	83	W
Operating Junction Temperature	TJ	(Note 1)	-20 ~ 125	°C

Control Part

Item	Symbol	Condition	Rating	Unit
Control Supply Voltage	V _{CC}	Applied between V _{CC} - COM	20	V
Input Signal Voltage	V _{IN}	Applied between IN - COM	-0.3~5.5	V
Fault Output Supply Voltage	V_{FO}	Applied between V _{FO} - COM	-0.3~V _{CC} +0.3	V
Fault Output Current I _{FO}		Sink Current at V _{FO} Pin	5	mA
Current Sensing Input Voltage V _{SC}		Applied between C _{SC} - COM	-0.3~V _{CC} +0.3	V

Total System

Item	Symbol	Condition	Rating	Unit
Module Case Operation Temperature	T _C		-20 ~ 100	°C
Storage Temperature	T _{STG}		-40 ~ 125	°C
Isolation Voltage	V _{ISO}	60Hz, Sinusoidal, AC 1 minute, Connection Pins to DBC	2500	V _{rms}

Thermal Resistance

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Junction to Case Thermal	$R_{\theta(j-c)Q}$	IGBT	-	-	1.2	°C/W
Resistance	$R_{\theta(j-c)HD}$	High-side diode	-	-	2.0	°C/W
(Referenced to PKG center)	$R_{\theta(j-c)LD}$	Low-side diode	-	-	1.4	°C/W

2. For the measurement point of case temperature($T_{\mbox{\scriptsize C}}$), please refer to Fig. 2.

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Note 1. The maximum junction temperature rating of the power chips integrated within the SPM is 150 °C(@ $T_C \le 100$ °C). However, to insure safe operation of the SPM, the average junction temperature should be limited to $T_{J(ave)} \le 125$ °C (@ $T_C \le 100$ °C)

Electrical Characteristics (T_J = 25°C, Unless Otherwise Specified)

Converter Part

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
IGBT saturation voltage	V _{CE(sat)}	$V_{CC} = 15V, V_{IN} = 5V; I_{C} = 30A$	-	2.4	3.1	V
High-side diode voltage	V_{FH}	I _F = 30A	-	1.9	2.5	V
Low-side diode voltage	V_{FL}	I _F = 30A	-	1.2	1.6	V
Switching Times	t _{ON}	V_{PN} = 400V, V_{CC} = 15V, I_{C} =30A V_{IN} = 0V \leftrightarrow 5V, Inductive Load	-	550	-	ns
	t _{C(ON)}		-	200	-	ns
	t _{OFF}	(Note 3)	-	430	-	ns
	t _{C(OFF)}	(1000 0)	-	180	-	ns
	t _{rr}		-	60	-	ns
	I _{rr}		-	6	-	Α
Collector - emitter Leakage Current	I _{CES}	V _{CE} = V _{CES}	-	-	250	μА

Control Part

Item	Symbol	Co	ondition	Min.	Тур.	Max.	Unit
Quiescent V _{CC} Supply Current	I _{QCCL}	V _{CC} = 15V, IN = 0V	V _{CC} - COM	-	-	26	mA
Fault Output Voltage	V _{FOH}	V _{SC} = 0V, V _{FO} Circuit	t: 4.7kΩ to 5V Pull-up	4.5	-	-	V
	V _{FOL}	V_{SC} = 1V, V_{FO} Circuit: 4.7k Ω to 5V Pull-up		-	-	0.8	V
Over Current Trip Level	V _{SC(ref)}	V _{CC} = 15V	0.45	0.5	0.55	V	
Supply Circuit Under-	UV _{CCD}	Detection Level		10.7	11.9	13.0	V
Voltage Protection	UV _{CCR}	Reset Level		11.2	12.4	13.2	V
Fault-out Pulse Width	t _{FOD}	C _{FOD} = 33nF (Note 4	1.4	1.8	2.0	ms	
ON Threshold Voltage	V _{IN(ON)}	Applied between IN -	3.0	-	-	V	
OFF Threshold Voltage	V _{IN(OFF)}]	-	-	0.8	V	
Resistance of Thermistor	R _{TH}	@ T _C = 25°C (Note Fig. 9)		-	50	-	kΩ
		@ T _C = 80°C (Note F	ig. 9)	-	5.76	-	kΩ

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Note
3. toN and toFF include the propagation delay time of the internal drive IC. to(ON) and to(OFF) are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Fig. 4

Note 4. The fault-out pulse width t_{FOD} depends on the capacitance value of C_{FOD} according to the following approximate equation : $C_{FOD} = 18.3 \times 10^{-6} \times t_{FOD}[F]$

Electrical Characteristics

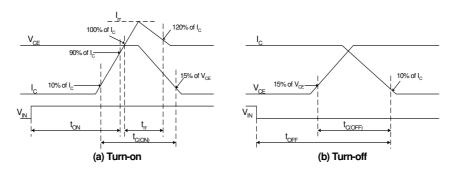


Fig. 4. Switching Time Definition

Mechanical Characteristics and Ratings

Item		Limits			Units	
nem	'	Min.	Тур.	Max.	Units	
Mounting Torque	Mounting Screw: - M3	Recommended 0.62N•m	0.51	0.62	0.72	N•m
Device Flatness	Note Fig. 5	0	-	+120	μm	
Weight			-	15.00	-	g

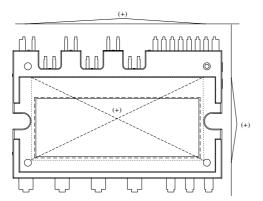
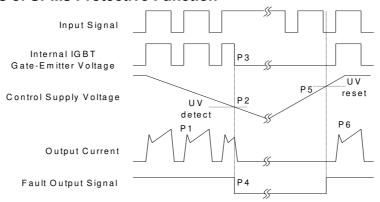


Fig. 5. Flatness Measurement Position

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Time Charts of SPMs Protective Function

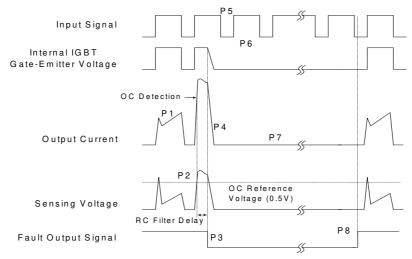


P1: Normal operation - IGBT ON and conducting current

P2: Under voltage detection P3: IGBT gate interrupt P4: Fault signal generation P5: Under voltage reset

P6: Normal operation - IGBT ON and conducting current

Fig. 6. Under-Voltage Protection



P1: Normal operation - IGBT ON and conducting current

P2 : Over current detection

P3: IGBT gate interrupt / Fault signal generation

P4: IGBT is slowly turned off

P5 : IGBT OFF signal

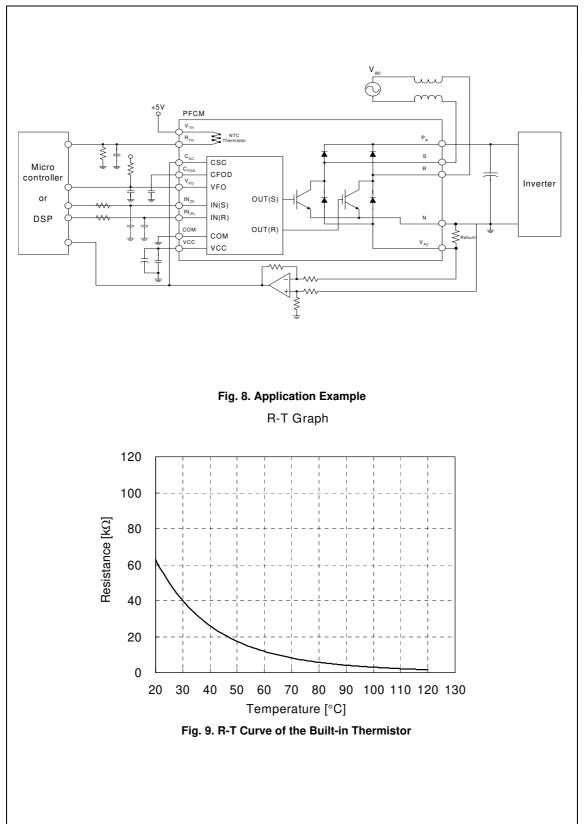
P6: IGBT ON signal - but IGBT cannot be turned on during the fault Output activation

P7: IGBT OFF state

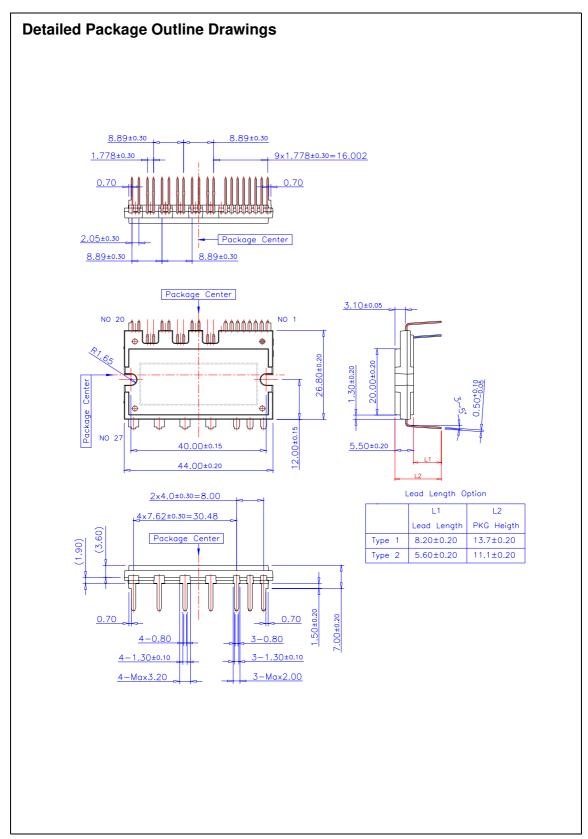
P8 : Fault Output reset and normal operation start

Fig. 7. Over Current Protection

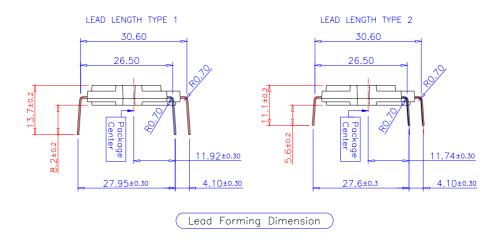
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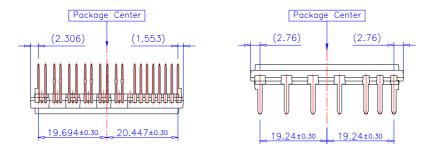


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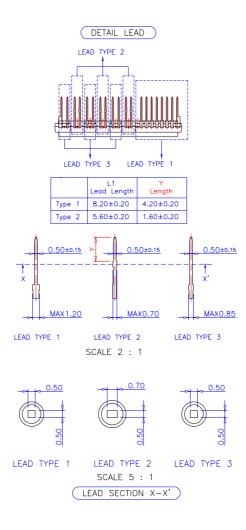
Detailed Package Outline Drawings





PKG Center to Lead Distance

Detailed Package Outline Drawings



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